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PTO/SB/08a/b (07-05)

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Substitute for form 1449A/B/PTO			Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Application Number	09/855,532-Conf. #8772
			Filing Date	May 16, 2001
			First Named Inventor	Joseph E. Geusic
			Art Unit	2828
			Examiner Name	A. Rodriguez
			Attorney Docket Number	M4065.0439/P439
Sheet	1	of	1	

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Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number/Kind Code ² (if known)			
AC		US-2003/0131782 ✓	7-2003	Geusic et al.	
		US-2003/0133683 ✓	7-2003	Forbes et al.	
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		US-2005/0029501 ✓	2-2005	Geusic et al.	
		US-2005/0029683 ✓	2-2005	Forbes et al.	
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NON PATENT LITERATURE DOCUMENTS				
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¹ Applicant's unique citation designation number (optional). ³ Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	Armando Rodriguez	Date Considered	3-27-06
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3-22-06

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		Art Unit	2828
		Examiner Name	A. Rodriguez
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		Attorney Docket Number	M4065.0439/P439

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	AW	5,646,053	07-1997	Schepis	
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Examiner Signature	Amanda Rodriguez			Date Considered	3-31-06

DSMDB.2060069.1

PTO/SB/08a/b (07-05)

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Sheet	2	of	10

AT1	6,001,711	12-1999	Hashimoto
AU1	6,013,970	01-2000	Nishikawa, et al.
AV1	6,016,000	01-2000	Moslehi
AW1	6,016,001	01-2000	Sanchez, et al.
AX1	6,022,793	02-2000	Wijaranakula, et al.
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AA2	6,069,064	05-2000	Cutter, et al.
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AD2	6,083,324	07-2000	Henley, et al.
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AI2	6,097,077	08-2000	Gordon, et al.
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AK3	6,344,373	02-2002	Bhattacharyya, et al.
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AO3	6,377,070	04-2002	Forbes

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	AW3	6,444,534	09-2002	Maszara	
	AX3	6,444,558	09-2002	Cutter, et al.	
	AY3	6,448,601	09-2002	Forbes, et al.	
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	AA4	6,456,149	09-2002	Cutter, et al.	
	AB4	6,458,630	10-2002	Daubenspeck, et al.	
	AC4	6,461,933	10-2002	Houston	
	AD4	6,478,883	11-2002	Tamatsuka, et al.	
	AE4	6,495,395	12-2002	Reinberg	
	AF4	6,496,034	12-2002	Forbes, et al.	
	AG4	6,498,056	12-2002	Motsiff, et al.	
	AH4	6,509,623	01-2003	Zhao	
	AI4	6,525,399	02-2003	Cutter, et al.	
	AJ4	6,531,727	03-2003	Forbes, et al.	
	AK4	6,538,330	03-2003	Forbes	
	AL4	6,541,356	04-2003	Fogel, et al.	
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	AO4	6,559,491	05-2003	Forbes, et al.	
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	AR4	6,582,512	06-2003	Geusic, et al.	
	AS4	6,583,437	06-2003	Mizuno, et al.	
	AT4	6,589,334	07-2003	John, et al.	
	AU4	6,593,625	07-2003	Christiansen, et al.	
	AV4	6,597,203	07-2003	Forbes	
	AW4	6,630,713	10-2003	Geusic	
	AX4	6,630,724	10-2003	Marr	
	AY4	6,649,476	11-2003	Forbes	
	AZ4	6,656,822	12-2003	Doyle, et al.	
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	AB5	6,674,667	01-2004	Forbes	
	AC5	6,740,913	05-2004	Doyle, et al.	
	AD5	6,943,065	09-2005	Bhattacharyya, et al.	
	AE5	2002/0001965	01/2002	Forbes	
	AF5	2002/0048968	04/2002	Ahn	
	AG5	2002/0062782	05/2002	Norris, et al.	
	AH5	2002/0070419	06/2002	Farrar, et al.	
	AI5	2002/0070421	06/2002	Ashburn	
	AJ5	2002/0076896	06/2002	Farrar, et al.	
AL	AK5	2002/0079557	06/2002	Ahn, et al.	

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		Art Unit	2828
		Examiner Name	A. Rodriguez
Sheet	4	of	10
		Attorney Docket Number	M4065.0439/P439

AL5	2002/0175330	11/2002	Geusic, et al.
AM5	2002/0182837	12/2002	Daubenspeck, et al.
AN5	2002/0185686	12/2002	Christiansen, et al.
AO5	2003/0027406	02/2003	Malone
AP5	2003/0042534	08/2001	Bhattacharyya
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AR5	2003/0071324	05/2003	Motsiff, et al.
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Examiner Signature	Armando Rodriguez		Date Considered 3-31-06

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		Attorney Docket Number	M4065.0439/P439

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		Examiner Name	A. Rodriguez		
Sheet	6	of	10	Attorney Docket Number	M4065.0439/P439

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Examiner Signature	<i>Armando Rodriguez</i>	Date Considered	3-31-06
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Substitute for form 1449A/B/PTO		Complete If Known	
		Application Number	09/855,532-Conf. #9772
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Filing Date	May 16, 2001
		First Named Inventor	Joseph E. Geusic
		Art Unit	2828
		Examiner Name	A. Rodriguez
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Examiner Signature	Hamande Rodriguez	
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		First Named Inventor	Joseph E. Geusic
		Art Unit	2828
		Examiner Name	A. Rodriguez
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Examiner Signature	Amanda Rodriguez	
Date Considered	3-31-06	

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			Art Unit	2828
			Examiner Name	A. Rodriguez
			Attorney Docket Number	M4065.0439/P439
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Examiner Signature		Armando Rodriguez	Date Considered 3-31-06

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		Art Unit	2828
		Examiner Name	A. Rodriguez
		Attorney Docket Number	M4065.0439/P439
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Examiner Signature	<i>A. Rodriguez</i>	Date Considered	3-31-06
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